

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	$I_D$ $T_C = +25^\circ C$
100V	140m $\Omega$ @ $V_{GS} = 10V$	12A
	160m $\Omega$ @ $V_{GS} = 4.5V$	11A

## Description

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## Applications

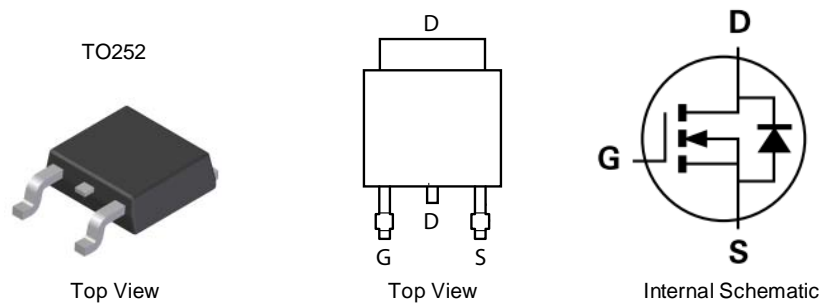
- DC-DC Converters
- Power management functions
- Analog Switch

## Features

- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208  $\text{\textcircled{3}}$
- Weight: 0.33 grams (approximate)

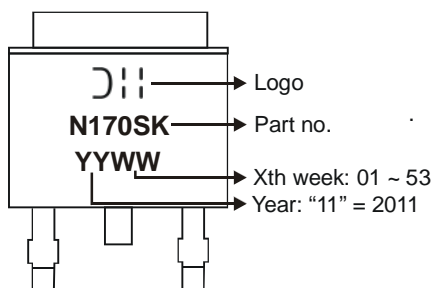


## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H170SK3-13	TO252	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	100	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 4) V <sub>GS</sub> = 10V	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	12	A
		T <sub>C</sub> = +100°C		7.5	
Maximum Body Diode Forward Current (Note 4)			I <sub>S</sub>	4	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I <sub>DM</sub>	16	A
Avalanche Current (Note 5)			I <sub>AR</sub>	5.3	A
Avalanche Energy (Note 5)			E <sub>AR</sub>	20	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 4)	T <sub>C</sub> = +25°C	P <sub>D</sub>	42	W
	T <sub>C</sub> = +100°C		17	
Thermal Resistance, Junction to Ambient (Note 4)		R <sub>θJA</sub>	44	°C/W
Thermal Resistance, Junction to Case (Note 4)		R <sub>θJC</sub>	3	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes: 4. Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper pad layout.  
5. UIS in production with L = 1.43mH, T<sub>J</sub> = +25°C.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 6)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 100V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 6)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	—	3.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	—	99	140	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 5A
		—	104	160		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 5A
Diode Forward Voltage	V <sub>SD</sub>	—	0.7	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10A
<b>DYNAMIC CHARACTERISTICS (Note 7)</b>						
Input Capacitance	C <sub>iss</sub>	—	1167	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	36	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	25	—		
Gate Resistance	R <sub>G</sub>	—	1.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	4.9	—	nC	V <sub>DS</sub> = 80V, I <sub>D</sub> = 12.8A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	9.7	—		
Gate-Source Charge	Q <sub>gs</sub>	—	2.0	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.0	—		
Turn-On Delay Time	t <sub>D(on)</sub>	—	10.5	—	ns	V <sub>DD</sub> = 50V, R <sub>G</sub> = 25Ω, I <sub>D</sub> = 12.8A
Turn-On Rise Time	t <sub>r</sub>	—	11.1	—		
Turn-Off Delay Time	t <sub>D(off)</sub>	—	42.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	12.8	—		
Body Diode Reverse Recovery Time	t <sub>rr</sub>	—	30.3	—	ns	V <sub>GS</sub> = 0V, I <sub>S</sub> = 12.8A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	—	35.2	—	nC	V <sub>GS</sub> = 0V, I <sub>S</sub> = 12.8A, dI/dt = 100A/μs

Notes: 6. Short duration pulse test used to minimize self-heating effect  
7. Guaranteed by design; not subject to production testing

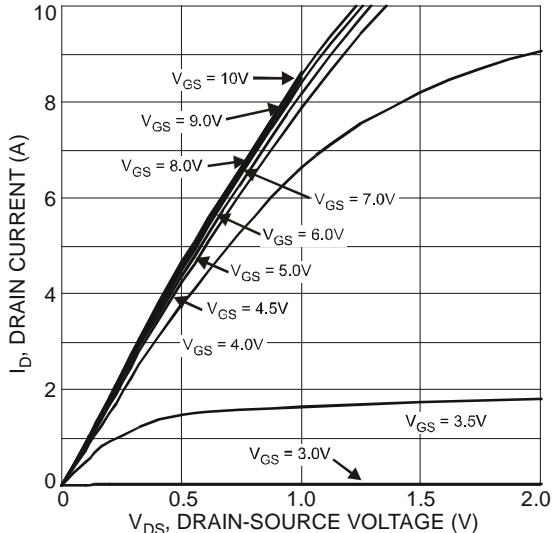


Fig. 1 Typical Output Characteristic

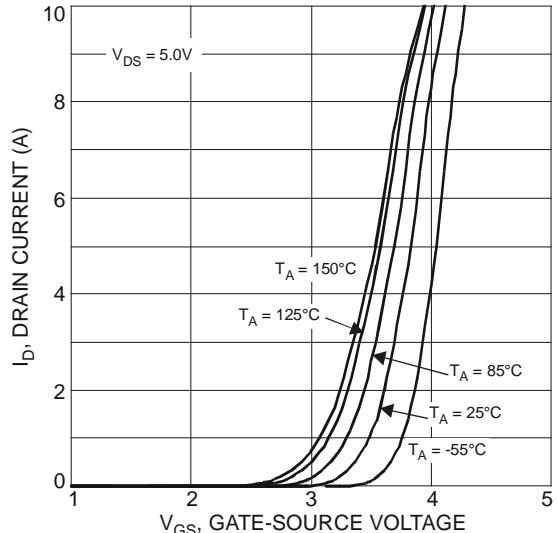


Fig. 2 Typical Transfer Characteristics

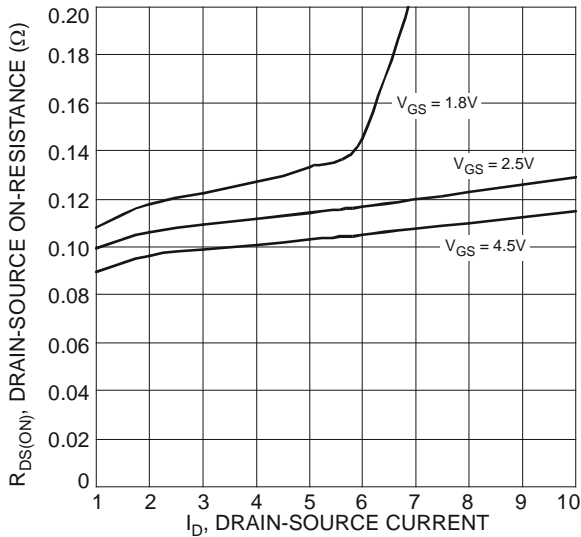


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

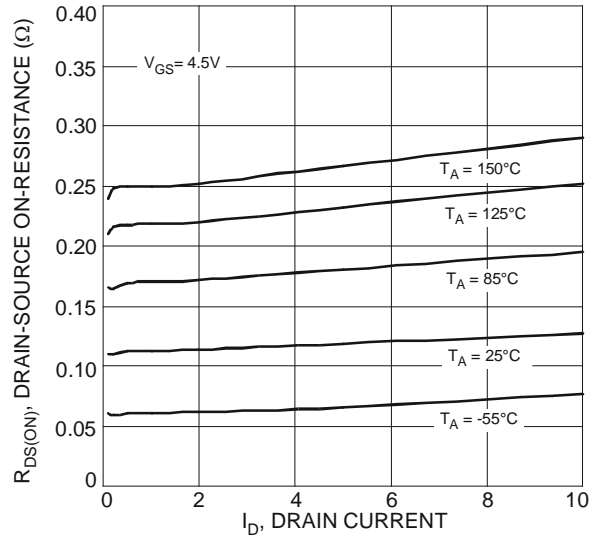


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

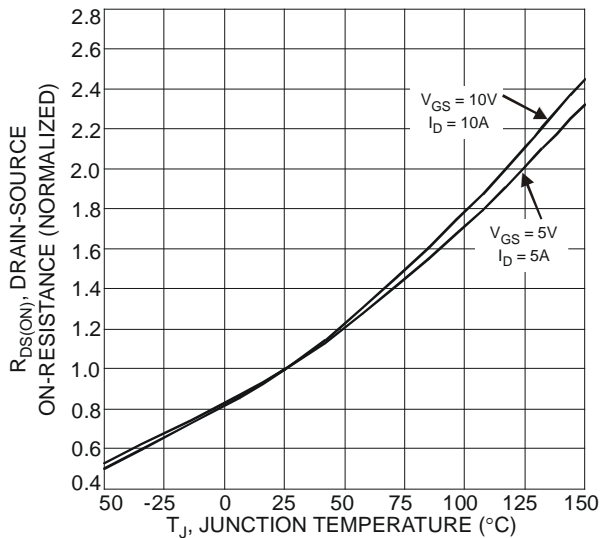


Fig. 5 On-Resistance Variation with Temperature

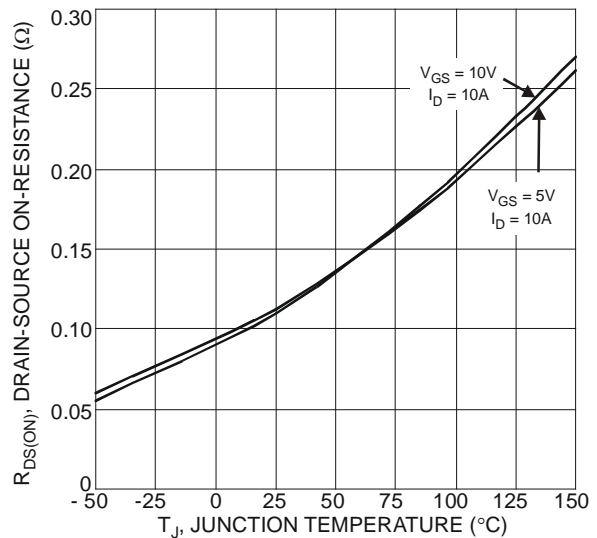


Fig. 6 On-Resistance Variation with Temperature

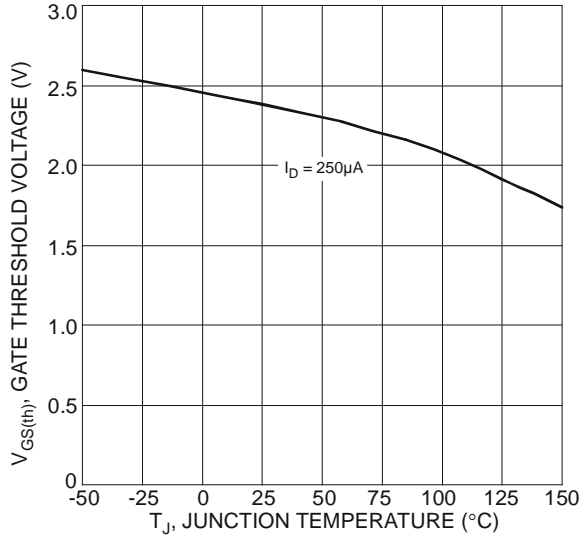


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

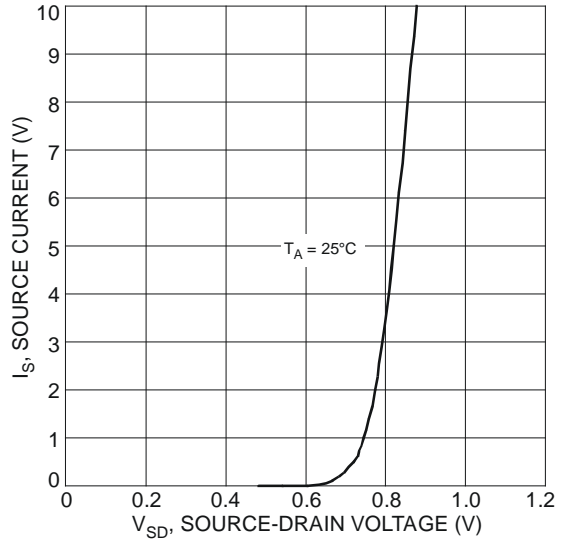


Fig.8 Diode Forward Voltage vs. Current

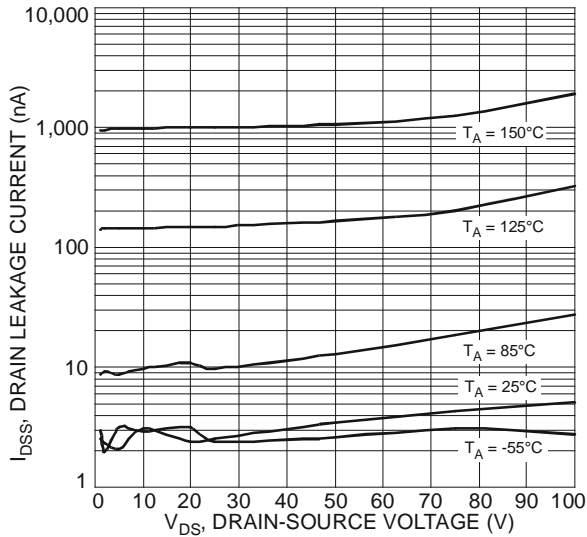


Fig. 9 Typical Drain-Source Leakage Current vs. Voltage

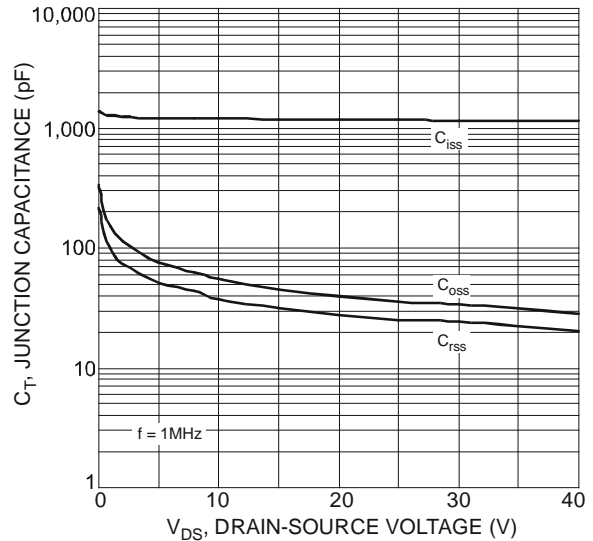


Fig. 10 Typical Junction Capacitance

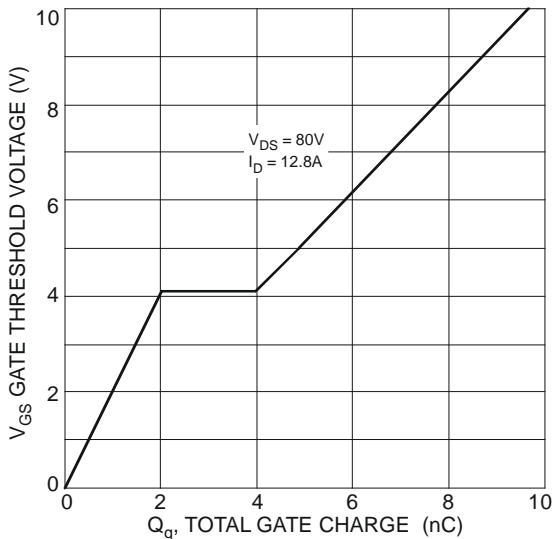
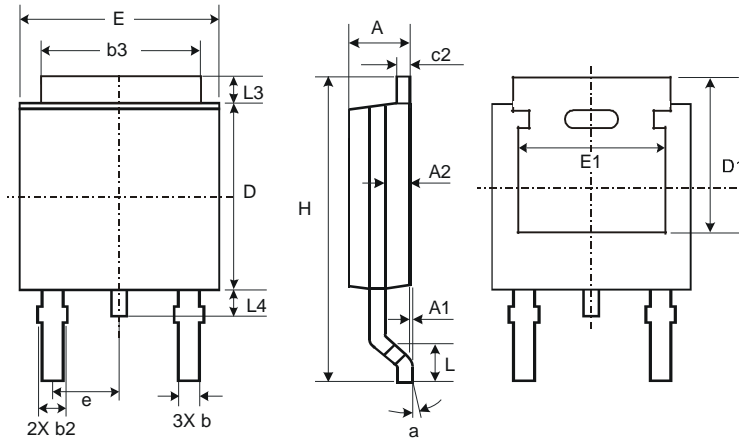


Fig. 11 Gate Charge

## Package Outline Dimensions

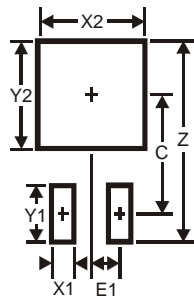
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



TO252			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c2	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	–	–
e	–	–	2.286
E	6.45	6.70	6.58
E1	4.32	–	–
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	–
<b>All Dimensions in mm</b>			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	11.6
X1	1.5
X2	7.0
Y1	2.5
Y2	7.0
C	6.9
E1	2.3

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